### Freescale Semiconductor

Data Sheet: Technical Data

Document Number: MC9RS08KA8 Rev. 4, 6/2009

# MC9RS08KA8

MC9RS08KA8 Series Covers: MC9RS08KA8

## MC9RS08KA4

#### Features:

- 8-Bit RS08 Central Processor Unit (CPU)
  - Up to 20 MHz CPU at 1.8 V to 5.5 V across temperature range of -40°C to 85°C
  - Subset of HC08 instruction set with added BGND instruction
- On-Chip Memory
  - 8 KB flash read/program/erase over full operating voltage and temperature; KA4 has 4 KB flash
  - 254 byte random-access memory (RAM); KA4 has 126 byte RAM
  - Security circuitry to prevent unauthorized access to RAM and flash contents
- · Power-Saving Modes
  - Wait and stop
  - Wakeup from power-saving modes using real-time interrupt (RTI), KBI, or ACMP
- Clock Source Options
  - Oscillator (XOSC) Loop-Control Pierce oscillator; crystal or ceramic resonator range of 31.25 kHz to 39.0625 kHz or 1 MHz to 5 MHz
  - Internal Clock Source (ICS) Internal clock source module containing a frequency-locked-loop (FLL) controlled by internal or external reference; precision trimming of internal reference allows 0.2% resolution and 2% deviation over temperature and voltage; supports bus frequencies up to 10 MHz
- System Protection
  - Watchdog computer operating properly (COP) reset with option to run from dedicated 1 kHz internal clock source or bus clock
  - Low-Voltage detection with reset or interrupt
  - Illegal opcode detection with reset
  - Illegal address detection with reset
  - Flash block protection
- Development Support

20-Pin W-SOIC Case 751D

20-Pin PDIP Case 738C

Case 948F

16-Pin TSSOP



16-Pin PDIP Case 648

Case 751G

16-Pin W-SOIC

- Single-Wire background debug interface
- Breakpoint capability to allow single breakpoint setting during in-circuit debugging
- Peripherals
  - ADC 12-channel, 10-bit resolution; 2.5 μs conversion time; automatic compare function; operation in stop; fully functional from 2.7 V to 5.5 V (8-channels available on 16-pin package)
  - TPM One 2-channel; selectable input capture, output compare, or buffered edge- or center-aligned PWM on each channel
  - IIC Inter-Integrated circuit bus module capable of operation up to 100 kbps with maximum bus loading; capable of higher baudrates with reduced loading
  - MTIM1 and MTIM2 Two 8-bit modulo timers
  - KBI Keyboard interrupts with rising or falling edge detect; eight KBI ports in 16-pin and 20-pin packages
  - ACMP Analog comparator: full rail-to-rail supply operation; option to compare to fixed internal bandgap reference voltage; can operate in stop mode
- Input/Output
  - 14/18 GPIOs including one output only pin and one input only pin
  - Hysteresis and configurable pullup device on all input pins; configurable slew rate and drive strength on all output pins
- · Package Options
  - 16-pin SOIC, PDIP or TSSOP
  - 20-pin SOIC or PDIP

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# **Revision History**

To provide the most up-to-date information, the revision of our documents on the World Wide Web will be the most current. Your printed copy may be an earlier revision. To verify you have the latest information available, refer to:

http://freescale.com/

The following revision history table summarizes changes contained in this document.

Revision	Date	Description of Changes	
1	1/22/2008	Initial public release	
2	10/7/2008	Updated Figure 4 and Figure 10. Updated "How to Reach Us" information. Added 16-pin TSSOP package information.	
3	11/4/2008	Updated operating voltage in Table 7.	
4	6/11/2009	Added output voltage of high drive at 5 V, $I_{load} = 10$ mA in the Table 7.	

## **Related Documentation**

Find the most current versions of all documents at: http://www.freescale.com

### Reference Manual (MC9RS08KA8RM)

Contains extensive product information including modes of operation, memory, resets and interrupts, register definition, port pins, CPU, and all module information.

# 1 MCU Block Diagram

The block diagram, Figure 1, shows the structure of the MC9RS08KA8 MCU.

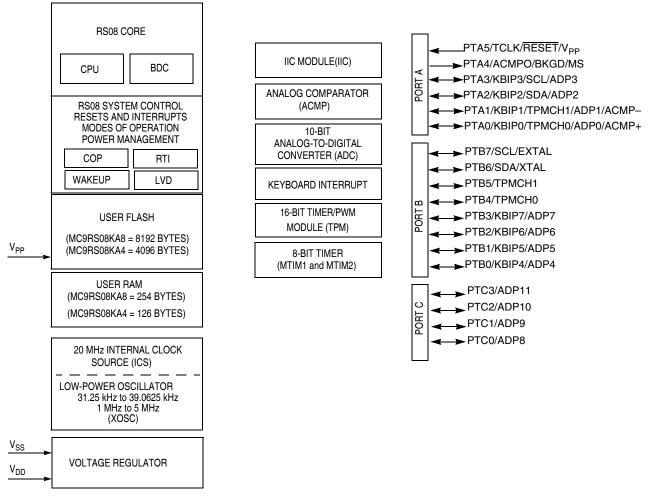


Figure 1. MC9RS08KA8 Series Block Diagram

# 2 Pin Assignments

This section shows the pin assignments in the packages available for the MC9RS08KA8 series.

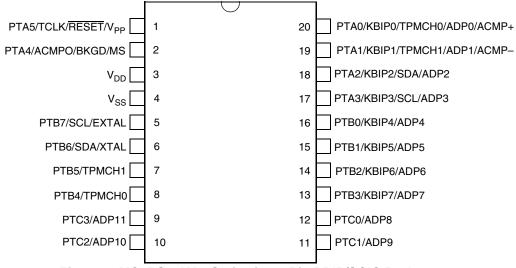
#### **Pin Assignments**

Pin Number			< Low	est <b>Priority</b>	> Highest	
20	16	Port Pin	Alt 1	Alt 2	Alt 3	Alt 4
1	1	PTA5		TCLK	RESET	V <sub>PP</sub>
2	2	PTA4	ACMPO	BKGD	MS	
3	3					V <sub>DD</sub>
4	4					V <sub>SS</sub>
5	5	PTB7	SCL <sup>1</sup>			EXTAL
6	6	PTB6	SDA <sup>1</sup>			XTAL
7	7	PTB5	TPMCH1 <sup>2</sup>			
8	8	PTB4	TPMCH0 <sup>2</sup>			
9	_	PTC3			ADP11	
10	_	PTC2			ADP10	
11	_	PTC1			ADP9	
12	_	PTC0			ADP8	
13	9	PTB3	KBIP7		ADP7	
14	10	PTB2	KBIP6		ADP6	
15	11	PTB1	KBIP5		ADP5	
16	12	PTB0	KBIP4		ADP4	
17	13	PTA3	KBIP3	SCL <sup>1</sup>	ADP3	
18	14	PTA2	KBIP2	SDA <sup>1</sup>	ADP2	
19	15	PTA1	KBIP1	TPMCH1 <sup>2</sup>	ADP1	ACMP-
20	16	PTA0	KBIP0	TPMCH0 <sup>2</sup>	ADP0	ACMP+

 Table 1. Pin Availability by Package Pin-Count

<sup>1</sup> IIC pins can be remapped to PTA3 and PTA2

<sup>2</sup> TPM pins can be remapped to PTA0 and PTA1





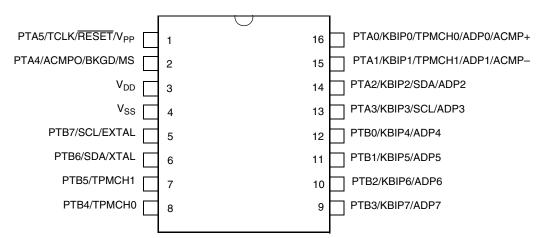


Figure 3. MC9RS08KA8 Series in 16-Pin PDIP/SOIC/TSSOP Package

## **3** Electrical Characteristics

### 3.1 Introduction

This chapter contains electrical and timing specifications for the MC9RS08KA8 series of microcontrollers available at the time of publication.

### 3.2 Parameter Classification

The electrical parameters shown in this supplement are guaranteed by various methods. To give the customer a better understanding the following classification is used and the parameters are tagged accordingly in the tables where appropriate:

Table 2. Parameter C	lassifications
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Р	Those parameters are guaranteed during production testing on each individual device.
С	Those parameters are achieved by the design characterization by measuring a statistically relevant sample size across process variations.
т	Those parameters are achieved by design characterization on a small sample size from typical devices under typical conditions unless otherwise noted. All values shown in the typical column are within this category.
D	Those parameters are derived mainly from simulations.

### NOTE

The classification is shown in the column labeled "C" in the parameter tables where appropriate.

## 3.3 Absolute Maximum Ratings

Absolute maximum ratings are stress ratings only, and functional operation at the maxima is not guaranteed. Stress beyond the limits specified in Table 3 may affect device reliability or cause permanent damage to the device. For functional operating conditions, refer to the remaining tables in this chapter.

This device contains circuitry protecting against damage due to high static voltage or electrical fields; however, it is advised that normal precautions be taken to avoid application of any voltages higher than maximum-rated voltages to this high-impedance circuit. Reliability of operation is enhanced if unused inputs are tied to an appropriate logic voltage level (for instance,  $V_{SS}$  or  $V_{DD}$ ) or the programmable pull-up resistor associated with the pin is enabled.

Rating	Symbol	Value	Unit
Supply voltage	V <sub>DD</sub>	–0.3 to 5.8	V
Maximum current into V <sub>DD</sub>	I <sub>DD</sub>	120	mA
Digital input voltage	V <sub>In</sub>	–0.3 to V <sub>DD</sub> + 0.3	V
Instantaneous maximum current Single pin limit (applies to all port pins) <sup>1, 2, 3</sup>	I <sub>D</sub>	±25	mA
Storage temperature range	T <sub>stg</sub>	–55 to 150	°C

Table 3. Absolute Maximum Ratings

<sup>1</sup> Input must be current limited to the value specified. To determine the value of the required current-limiting resistor, calculate resistance values for positive (V<sub>DD</sub>) and negative (V<sub>SS</sub>) clamp voltages, then use the larger of the two resistance values.

<sup>2</sup> All functional non-supply pins are internally clamped to V<sub>SS</sub> and V<sub>DD</sub> except the  $\overline{\text{RESET}}/V_{PP}$  pin which is internally clamped to V<sub>SS</sub> only.

<sup>3</sup> Power supply must maintain regulation within operating V<sub>DD</sub> range during instantaneous and operating maximum current conditions. If positive injection current ( $V_{In} > V_{DD}$ ) is greater than  $I_{DD}$ , the injection current may flow out of  $V_{DD}$  and could result in external power supply going out of regulation. Ensure external VDD load will shunt current greater than maximum injection current. This will be the greatest risk when the MCU is not consuming power. Examples are: if no system clock is present, or if the clock rate is very low which would reduce overall power consumption.

## 3.4 Thermal Characteristics

This section provides information about operating temperature range, power dissipation, and package thermal resistance. Power dissipation on I/O pins is usually small compared to the power dissipation in on-chip logic and voltage regulator circuits and it is user-determined rather than being controlled by the MCU design. In order to take  $P_{I/O}$  into account in power calculations, determine the difference between actual pin voltage and  $V_{SS}$  or  $V_{DD}$  and multiply by the pin current for each I/O pin. Except in cases of unusually high pin current (heavy loads), the difference between pin voltage and  $V_{SS}$  or  $V_{DD}$  will be very small.

Rating	Symbol	Value	Unit
Operating temperature range (packaged)	T <sub>A</sub>	T <sub>L</sub> to T <sub>H</sub> –40 to 85	°C
Maximum junction temperature	T <sub>JMAX</sub>	105	°C
Thermal resistance 16-pin PDIP	$\theta_{JA}$	80	°C/W
Thermal resistance 16-pin SOIC	$\theta_{JA}$	112	°C/W

Rating	Symbol	Value	Unit
Thermal resistance 16-pin TSSOP	$\theta_{JA}$	75	°C/W
Thermal resistance 20-pin PDIP	$\theta_{JA}$	75	°C/W
Thermal resistance 20-pin SOIC	$\theta_{JA}$	96	°C/W

Table 4. Thermal Characteristics (continued)

The average chip-junction temperature (TJ) in °C can be obtained from:

where:

 $T_A$  = Ambient temperature, °C

 $\theta_{IA}$  = Package thermal resistance, junction-to-ambient, °C /W

$$P_D = P_{int} + P_{I/O}$$

 $P_{int} = I_{DD} \times V_{DD}$ , Watts chip internal power

 $P_{I/O}$  = Power dissipation on input and output pins user determined

For most applications,  $P_{I/O} \ll P_{int}$  and can be neglected. An approximate relationship between PD and TJ (if  $P_{I/O}$  is neglected) is:

$$P_{D} = K \div (T_{J} + 273^{\circ}C)$$
 Eqn. 2

Solving Equation 1 and Equation 2 for K gives:

$$K = P_{D} \times (T_{A} + 273^{\circ}C) + \theta_{JA} \times (PD)^{2}$$
 Eqn. 3

where K is a constant pertaining to the particular part. K can be determined from Equation 3 by measuring  $P_D$  (at equilibrium) for a known  $T_A$ . Using this value of K, the values of  $P_D$  and  $T_J$  can be obtained by solving equations 1 and 2 iteratively for any value of  $T_A$ .

### 3.5 ESD Protection and Latch-Up Immunity

Although damage from electrostatic discharge (ESD) is much less common on these devices than on early CMOS circuits, normal handling precautions must be used to avoid exposure to static discharge. Qualification tests are performed to ensure that these devices can withstand exposure to reasonable levels of static without suffering any permanent damage.

All ESD testing is in conformity with AEC-Q100 Stress Test Qualification for Automotive Grade Integrated Circuits. During the device qualification ESD stresses were performed for the human body model (HBM), the machine model (MM) and the charge device model (CDM).

A device is defined as a failure if after exposure to ESD pulses the device no longer meets the device specification. Complete DC parametric and functional testing is performed per the applicable device specification at room temperature followed by hot temperature, unless specified otherwise in the device specification.

Model	Description	Symbol	Value	Unit
	Series resistance	R1	1500	Ω
Human Body	Storage capacitance	С	100	pF
,	Number of pulses per pin	—	3	_
	Series resistance	R1	0	Ω
Machine	Storage capacitance	С	200	pF
	Number of pulses per pin	—	3	_
Latab up	Minimum input voltage limit	—	-2.5	V
Latch-up	Maximum input voltage limit	—	7.5	V

Table 5. ESD and Latch-up Test Conditions

Table 6. ESD and Latch-Up Protection Characterist	ics
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No.	Rating <sup>1</sup>	Symbol	Min	Max	Unit
1	Human body model (HBM)	V <sub>HBM</sub>	±2000	—	V
2	Machine model (MM)	V <sub>MM</sub>	±200	—	V
3	Charge device model (CDM)	V <sub>CDM</sub>	±500	—	V
4	Latch-up current at $T_A = 85^{\circ}C$ (applies to all pins except pin 9 PTC3/ADP11)	I <sub>LAT</sub>	±100 <sup>2</sup>	_	mA
	Latch-up current at $T_A = 85^{\circ}C$ (applies to pin 9 PTC3/ADP11)	I <sub>LAT</sub>	±75 <sup>3</sup>	_	mA

<sup>1</sup> Parameter is achieved by design characterization on a small sample size from typical devices under typical conditions unless otherwise noted.

 $^2~$  These pins meet JESD78A Class II (section 1.2) Level A (section 1.3) requirement of  $\pm 100 m A.$ 

<sup>3</sup> This pin meets JESD78A Class II (section 1.2) Level B (section 1.3) characterization to ±75mA. This pin is only present on 20 pin package types.

### 3.6 DC Characteristics

This section includes information about power supply requirements, I/O pin characteristics, and power supply current in various operating modes.

Parameter	Symbol	Min	Typical	Max	Unit
Supply voltage (run, wait and stop modes.) 0 < f <sub>Bus</sub> <10MHz V <sub>DD</sub> rising V <sub>DD</sub> falling	V <sub>DD</sub>	2.0 1.8	_	5.5	V
Minimum RAM retention supply voltage applied to $V_{DD}$	V <sub>RAM</sub>	0.8 <sup>1</sup>	_	—	V
Low-voltage Detection threshold (V <sub>DD</sub> falling) (V <sub>DD</sub> rising)	V <sub>LVD</sub>	1.80 1.88	1.86 1.94	1.95 2.03	V
Power on RESET (POR) voltage	V <sub>POR</sub> <sup>1</sup>	0.9	—	1.7	V

Parameter	Symbol	Min	Typical	Мах	Unit
Input high voltage (V <sub>DD</sub> > 2.3V) (all digital inputs)	V <sub>IH</sub>	$0.70 \times V_{DD}$	_	—	V
Input high voltage (1.8 V $\leq$ V <sub>DD</sub> $\leq$ 2.3 V) (all digital inputs)	V <sub>IH</sub>	$0.85 \times V_{DD}$	_	—	V
Input low voltage (V <sub>DD</sub> > 2.3 V) (all digital inputs)	V <sub>IL</sub>	—	_	$0.30 \times V_{DD}$	V
Input low voltage (1.8 V $\leq$ V <sub>DD</sub> $\leq$ 2.3 V) (all digital inputs)	V <sub>IL</sub>	—	_	$0.30 \times V_{DD}$	V
Input hysteresis (all digital inputs)	V <sub>hys</sub> <sup>1</sup>	$0.06 \times V_{DD}$	_	—	V
Input leakage current (per pin) $V_{In} = V_{DD}$ or $V_{SS}$ , all input only pins	llinl	—	0.025	1.0	μA
High impedance (off-state) leakage current (per pin) $V_{In} = V_{DD}$ or $V_{SS}$ , all input/output	llozl	—	0.025	1.0	μA
Internal pullup resistors <sup>2</sup> (all port pins)	R <sub>PU</sub>	20	45	65	kΩ
Internal pulldown resistors <sup>2</sup> (all port pins except PTA5)	R <sub>PD</sub>	20	45	65	kΩ
PTA5 Internal pulldown resistor	_	45	—	95	kΩ
Output high voltage — Low Drive (PTxDSn = 0) 5 V, I <sub>Load</sub> = 2 mA 3 V, I <sub>Load</sub> = 1 mA 1.8 V, I <sub>Load</sub> = 0.5 mA		V <sub>DD</sub> – 0.8		 	
Output high voltage — High Drive (PTxDSn = 1) 5 V, $I_{Load}$ = 10 mA 5 V, $I_{Load}$ = 5 mA 3 V, $I_{Load}$ = 3 mA 1.8 V, $I_{Load}$ = 2 mA	V <sub>OH</sub>	V <sub>DD</sub> – 0.8		 	V
Maximum total IOH for all port pins	II <sub>ОНТ</sub>	—		40	mA
Output low voltage — Low Drive (PTxDSn = 0) 5 V, $I_{Load} = 2 \text{ mA}$ 3 V, $I_{Load} = 1 \text{ mA}$ 1.8 V, $I_{Load} = 0.5 \text{ mA}$		 	 	0.8	
Output low voltage — High Drive (PTxDSn = 1) 5 V, $I_{Load}$ = 10 mA 5 V, $I_{Load}$ = 5 mA 3 V, $I_{Load}$ = 3 mA 1.8 V, $I_{Load}$ = 2 mA	V <sub>OL</sub>	 		0.8	V
Maximum total Io∟ for all port pins	I <sub>OLT</sub>	—	—	40	mA
DC injection current <sup>3, 4, 5,6</sup> V <sub>In</sub> < V <sub>SS</sub> , V <sub>In</sub> > V <sub>DD</sub> Single pin limit Total MCU limit, includes sum of all stressed pins			_	0.2 0.8	mA
Input capacitance (all non-supply pins)	C <sub>In</sub>	_	_	7	pF

<sup>1</sup> This parameter is characterized and not tested on each device.

 $^2~$  Measurement condition for pull resistors: V\_In = V\_{SS} for pullup and V\_In = V\_{DD} for pulldown.

<sup>3</sup> All functional non-supply pins are internally clamped to V<sub>SS</sub> and V<sub>DD</sub> except the RESET/V<sub>PP</sub> which is internally clamped to V<sub>SS</sub> only.

<sup>4</sup> Input must be current limited to the value specified. To determine the value of the required current-limiting resistor, calculate resistance values for positive and negative clamp voltages, then use the larger of the two values.

<sup>5</sup> Input must be current limited to the value specified. To determine the value of the required current-limiting resistor, calculate resistance values for positive and negative clamp voltages, then use the larger of the two values.

<sup>6</sup> This parameter is characterized and not tested on each device.

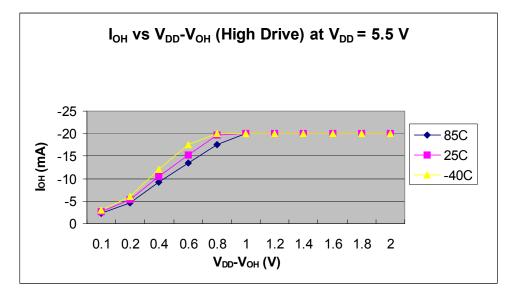


Figure 4. Typical  $I_{OH}$  vs.  $V_{DD}$ – $V_{OH}$  $V_{DD}$  = 5.5 V (High Drive)

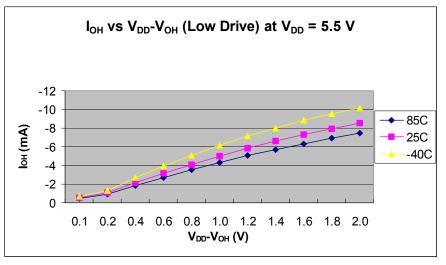


Figure 5. Typical I<sub>OH</sub> vs. V<sub>DD</sub>–V<sub>OH</sub> V<sub>DD</sub> = 5.5 V (Low Drive)

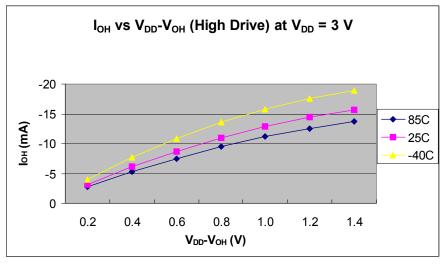


Figure 6. Typical  $I_{OH}$  vs.  $V_{DD}$ - $V_{OH}$  $V_{DD}$  = 3 V (High Drive)

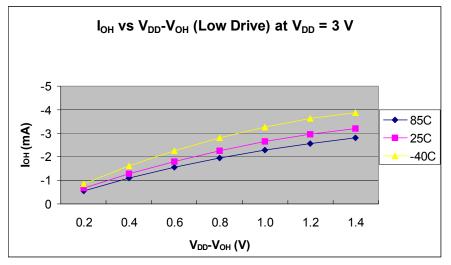


Figure 7. Typical  $I_{OH}$  vs.  $V_{DD}$ - $V_{OH}$  $V_{DD}$  = 3 V (Low Drive)

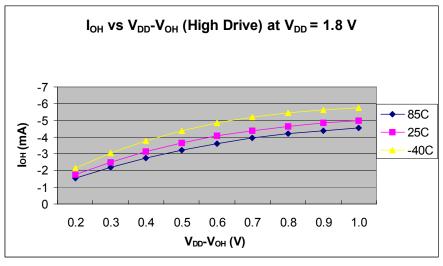


Figure 8. Typical  $I_{OH}$  vs.  $V_{DD}$ - $V_{OH}$  $V_{DD}$  = 1.8 V (High Drive)

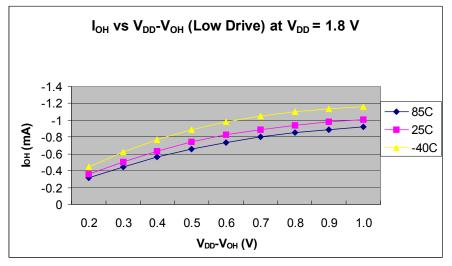


Figure 9. Typical I<sub>OH</sub> vs. V<sub>DD</sub>–V<sub>OH</sub> V<sub>DD</sub> = 1.8 V (Low Drive)

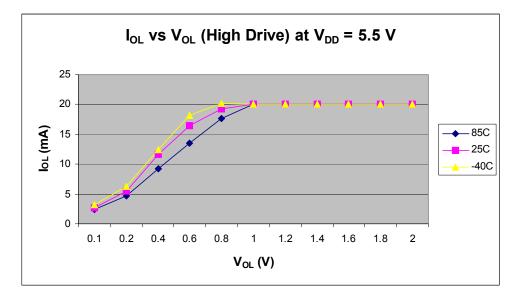


Figure 10. Typical I<sub>OL</sub> vs. V<sub>DD</sub>–V<sub>OL</sub> V<sub>DD</sub> = 5.5 V (High Drive)

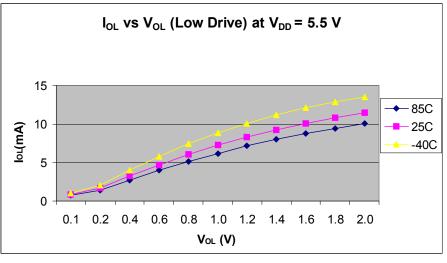


Figure 11. Typical I<sub>OL</sub> vs. V<sub>DD</sub>–V<sub>OL</sub>  $V_{DD}$  = 5.5 V (Low Drive)

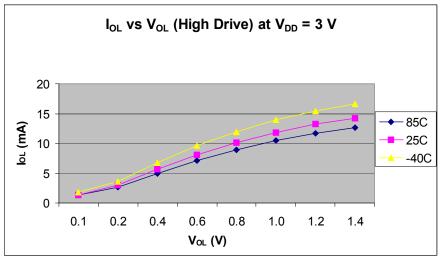


Figure 12. Typical  $I_{OL}$  vs.  $V_{DD}$ – $V_{OL}$  $V_{DD}$  = 3 V (High Drive)

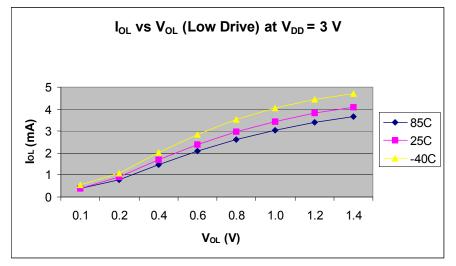


Figure 13. Typical  $I_{OL}$  vs.  $V_{DD}$ – $V_{OL}$  $V_{DD}$  = 3 V (Low Drive)

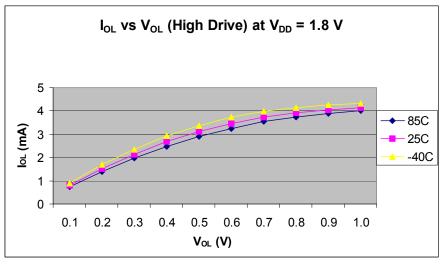


Figure 14. Typical I<sub>OL</sub> vs. V<sub>DD</sub>–V<sub>OL</sub> V<sub>DD</sub> = 1.8 V (High Drive)

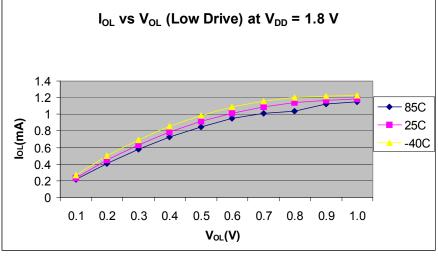


Figure 15. Typical I<sub>OL</sub> vs. V<sub>DD</sub>–V<sub>OL</sub> V<sub>DD</sub> = 1.8 V (Low Drive)

### 3.7 Supply Current Characteristics

Table 8.	Supply	Current	Characteristics
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Parameter	Symbol	V <sub>DD</sub> (V)	Typical <sup>1</sup>	Max <sup>2</sup>	Temp. (°C)
		5	2.4 mA	5 mA	25 85
Run supply current <sup>3</sup> measured at (f <sub>Bus</sub> = 10 MHz)	RI <sub>DD10</sub>	3	2.4 mA	_	25 85
		1.80	1.7 mA		25 85

Parameter	Symbol	V <sub>DD</sub> (V)	Typical <sup>1</sup>	Max <sup>2</sup>	Temp. (°C)
		5	0.42 mA	2 mA	25 85
Run supply current <sup>3</sup> measured at (f <sub>Bus</sub> = 1.25 MHz)	RI <sub>DD1</sub>	3	0.42 mA	_	25 85
		1.80	0.3 mA	_	25 85
		5	2.4 μA	5 μΑ 8 μΑ	25 85
Stop mode supply current	SI <sub>DD</sub>	3	2 μΑ	_	25 85
		1.80	1.5 μA	_	25 85
		5	128 μA	150 μΑ 165 μΑ	25 85
ADC adder from stop <sup>4</sup>	_	3	121 μA	_	25 85
		1.80	79 μA	_	25 85
	_	5	21 μA	22 μA	25 85
ACMP adder from stop (ACME = 1)		3	18.5 μA	_	25 85
		1.80	17.5 μA	_	25 85
		5	2.4 μA	2 μΑ	25 85
RTI adder from stop with 1 kHz clock source enabled <sup>5</sup>	_	3	1.9 μA	_	25 85
		1.80	1.5 μA	_	25 85
		5	2.1 μA	2 μΑ	25 85
RTI adder from stop with 1 MHz external clock source reference enabled	_	3	1.6 μA	_	25 85
GHADIEU		1.80	1.2 μA	_	25 85
		5	70 μA	80 μA	25 85
LVI adder from stop (LVDE=1 and LVDSE=1)	_	3	65 μΑ		25 85
		1.80	60 μA		25 85

### Table 8. Supply Current Characteristics (continued)

<sup>1</sup> Typicals are measured at 25°C.

 $^2$  Maximum value is measured at the nominal V<sub>DD</sub> voltage times 10% tolerance. Values given here are preliminary estimates prior to completing characterization.

<sup>3</sup> Not include any DC loads on port pins.
<sup>4</sup> Required asynchronous ADC clock and LVD to be enabled.

<sup>5</sup> Most customers are expected to find that auto-wakeup from stop can be used instead of the higher current wait mode. Wait mode typical is 1.3 mA at 3 V and 1 mA at 2 V with  $f_{Bus} = 1$  MHz.

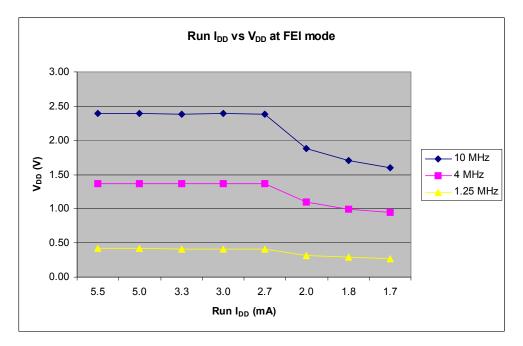


Figure 16. Typical Run  $I_{\text{DD}}$  vs.  $V_{\text{DD}}$  for FEI Mode

### 3.8 External Oscillator (XOSC) Characteristics

Table 9. Oscillator Electrical Specifications (Temperature Range = -40 to 125°C Ambient)

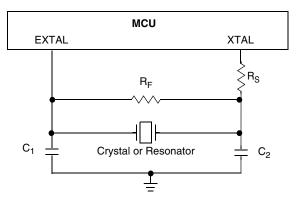
Num	С	Rating	Symbol	Min	Typical <sup>1</sup>	Max	Unit
1	С	Oscillator crystal or resonator (EREFS = 1, ERCLKEN = 1) Low range (RANGE = 0) High range (RANGE = 1) FEE or FBE mode <sup>2</sup> High range (RANGE = 1, HGO = 1) FBELP mode High range (RANGE = 1, HGO = 0) FBELP mode	f <sub>lo</sub> f <sub>hi</sub> f <sub>hi-hgo</sub> f <sub>hi-lp</sub>	32 1 1 1	 	38.4 5 16 8	kHz MHz MHz MHz
2	D	Load capacitors	C <sub>1,</sub> C <sub>2</sub>	See crystal or resonator manufacturer's recommendation.			or
3	D	Feedback resistor Low range (32 kHz to 100 kHz) High range (1 MHz to 16 MHz)	R <sub>F</sub>	_	10 1	_	MΩ
4	D	Series resistor Low range, low gain (RANGE = 0, HGO = 0) Low range, high gain (RANGE = 0, HGO = 1) High range, low gain (RANGE = 1, HGO = 0) High range, high gain (RANGE = 1, HGO = 1) ≥ 8 MHz 4 MHz 1 MHz	R <sub>S</sub>		0 100 0 0 0	  10 20	kΩ
5	С	Crystal start-up time <sup>3</sup> Low range, low gain (RANGE = 0, HGO = 0)		 	200 400 5 20		ms
6	D	Square wave input clock frequency (EREFS = 0, ERCLKEN = 1) FEE or FBE mode <sup>2</sup> FBELP mode	f <sub>extal</sub>	0.03125 0		5 40	MHz

<sup>1</sup> Typical data was characterized at 5.0 V, 25 °C or is recommended value.

<sup>2</sup> The input clock source must be divided using RDIV to within the range of 31.25 kHz to 39.0625 kHz.

<sup>3</sup> This parameter is characterized and not tested on each device. Proper PC board layout procedures must be followed to achieve specifications.

<sup>4</sup> 4 MHz crystal.



### 3.9 AC Characteristics

This section describes AC timing characteristics for each peripheral system.

### 3.9.1 Control Timing

Num	С	Parameter	Symbol	Min	Typical	Max	Unit
1	D	Bus frequency (t <sub>cyc</sub> = 1/f <sub>Bus</sub> )	f <sub>Bus</sub>	0	—	10	MHz
2	D	Real time interrupt internal oscillator period	t <sub>RTI</sub>	700	1000	1300	μS
3	D	External RESET pulse width <sup>1</sup>	t <sub>extrst</sub>	150	—	—	ns
4	D	KBI pulse width <sup>2</sup>	t <sub>KBIPW</sub>	1.5 t <sub>cyc</sub>	—	—	ns
5	D	KBI pulse width in stop <sup>1</sup>	t <sub>KBIPWS</sub>	100	—	—	ns
6	D	Port rise and fall time (load = 50 pF) <sup>3</sup> Slew rate control disabled (PTxSE = 0) Slew rate control enabled (PTxSE = 1)	t <sub>Rise</sub> , t <sub>Fall</sub>		11 35		ns

### Table 10. Control Timing

<sup>1</sup> This is the shortest pulse guaranteed to pass through the pin input filter circuitry. Shorter pulses may or may not be recognized.

<sup>2</sup> This is the minimum pulse width that is guaranteed to pass through the pin synchronization circuitry. Shorter pulses may or may not be recognized. In stop mode, the synchronizer is bypassed so shorter pulses can be recognized in that case.

 $^3$  Timing is shown with respect to 20%  $V_{DD}$  and 80%  $V_{DD}$  levels. Temperature range –40°C to 85°C.

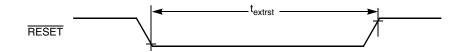


Figure 17. Reset Timing

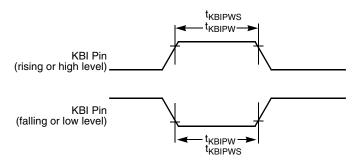


Figure 18. KBI Pulse Width

### 3.9.2 TPM/MTIM Module Timing

Synchronizer circuits determine the shortest input pulses that can be recognized or the fastest clock that can be used as the optional external source to the timer counter. These synchronizers operate from the current bus rate clock.

Num	С	Rating	Symbol	Min	Max	Unit
1	D	External clock frequency	f <sub>TPMext</sub>	DC	f <sub>Bus</sub> /4	MHz
2	D	External clock period	t <sub>TPMext</sub>	4	_	t <sub>cyc</sub>
3	D	External clock high time	t <sub>clkh</sub>	1.5	_	t <sub>cyc</sub>
4	D	External clock low time	t <sub>clkl</sub>	1.5	_	t <sub>cyc</sub>
5	D	Input capture pulse width	t <sub>ICPW</sub>	1.5	_	t <sub>cyc</sub>

Table 11. TPM Input Timing

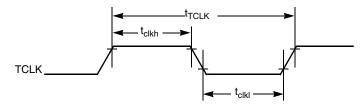


Figure 19. Timer External Clock

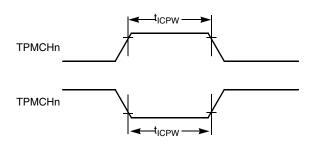


Figure 20. Timer Input Capture Pulse

### 3.10 Analog Comparator (ACMP) Electrical

### Table 12. Analog Comparator Electrical Specifications

Num	С	Characteristic	Symbol	Min	Typical	Max	Unit
1	D	Supply voltage	V <sub>DD</sub>	1.80	—	5.5	V
2	Р	Supply current (active)	I <sub>DDAC</sub>	_	20	35	μA
3	D	Analog input voltage <sup>1</sup>	V <sub>AIN</sub>	V <sub>SS</sub> – 0.3	—	V <sub>DD</sub>	V
4	Р	Analog input offset voltage <sup>1</sup>	V <sub>AIO</sub>	_	20	40	mV
5	С	Analog Comparator hysteresis <sup>1</sup>	V <sub>H</sub>	3.0	9.0	15.0	mV
6	С	Analog source impedance <sup>1</sup>	R <sub>AS</sub>	_	—	10	kΩ
7	Р	Analog input leakage current	I <sub>ALKG</sub>	_	—	1.0	μΑ
8	С	Analog Comparator initialization delay	t <sub>AINIT</sub>		—	1.0	μs

Num	С	Characteristic	Symbol	Min	Typical	Max	Unit
9	Ρ	Analog Comparator bandgap reference voltage	$V_{BG}$	1.1	1.208	1.3	V

Table 12. Analog Comparator Electrical Specifications (continued)

<sup>1</sup> These data are characterized but not production tested.

### 3.11 Internal Clock Source Characteristics

#### Num С Characteristic Symbol Min Typical<sup>1</sup> Max Unit 1 С Average internal reference frequency - untrimmed 25 31.25 41.66 kHz f<sub>int ut</sub> 2 Average internal reference frequency - trimmed 31.25 39.06 39.0625 kHz Ρ f<sub>int t</sub> 3 С DCO output frequency range - untrimmed 12.8 16 21.33 MHz f<sub>dco ut</sub> 4 Ρ DCO output frequency range - trimmed 16 20 20 MHz f<sub>dco\_t</sub> 5 С Resolution of trimmed DCO output frequency 0.2 %fdco \_\_\_\_ $\Delta f_{dco res t}$ at fixed voltage and temperature 6 С Total deviation of trimmed DCO output frequency 2 %fdco $\Delta f_{dco t}$ over voltage and temperature FLL acquisition time<sup>2,3</sup> 7 С 1 ms tacquire 8 С Stop recovery time (FLL wakeup to previous acquired frequency) t wakeup μS **IREFSTEN = 0** 100 **IREFSTEN = 1** 86

Table 13. Internal Clock Source Specifications

<sup>1</sup> Data in typical column was characterized at 3.0 V and 5.0 V, 25 °C or is typical recommended value.

<sup>2</sup> This parameter is characterized and not tested on each device.

<sup>3</sup> This specification applies to any time the FLL reference source or reference divider is changed, trim value changed or changing from FLL disabled (FBILP) to FLL enabled (FEI, FBI).

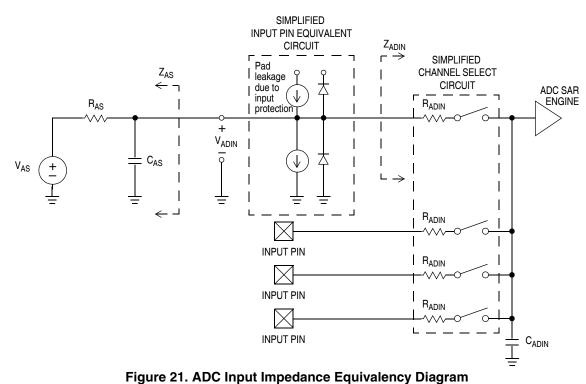
## 3.12 ADC Characteristics

### Table 14. 5 Volt 10-bit ADC Operating Conditions

С	Characteristic	Conditions	Symb	Min.	Typical	Max.	Unit
D	Input voltage	—	V <sub>ADIN</sub>	$V_{SS}$		$V_{DD}$	V
С	Accuracy	$V_{DD} = 2 V$	_	_	8 bit	_	—
С	Input capacitance	—	C <sub>ADIN</sub>	_	4.5	5.5	pF
С	Input resistance	—	R <sub>ADIN</sub>	_	3	5	kΩ
С	Analog source resistance external to MCU	10 bit mode f <sub>ADCK</sub> > 4MHz f <sub>ADCK</sub> < 4MHz	R <sub>AS</sub>	_	_	5 10	kΩ
		8 bit mode (all valid f <sub>ADCK</sub> )		_	—	10	

С	Characteristic	Conditions	Symb	Min.	Typical	Max.	Unit
D	ADC conversion clock	High Speed (ADLPC=0)	f	0.4	_	8.0	MHz
	frequency	Low Power (ADLPC=1)	TADCK	0.4		8.0	11112





Characteristic	Conditions	С	Symb	Min	Typical <sup>1</sup>	Мах	Unit
Supply current ADLPC = 1 ADLSMP = 1 ADCO = 1	_	т	I <sub>DDAD</sub>	_	133	_	μΑ
Supply current ADLPC = 1 ADLSMP = 0 ADCO = 1	_	т	I <sub>DDAD</sub>		218		μΑ
Supply current ADLPC = 0 ADLSMP = 1 ADCO = 1	_	т	I <sub>DDAD</sub>	_	327	_	μΑ
Supply current ADLPC = 0 ADLSMP = 0 ADCO = 1	_	с	I <sub>DDAD</sub>	_	0.582	1	mA

Table 15. 10-bit ADC Characteristics

Characteristic	Conditions	С	Symb	Min	Typical <sup>1</sup>	Max	Unit		
Supply current	Stop, reset, module off	т	I <sub>DDAD</sub>	—	0.011	1	μA		
ADC asynchronous clock	High speed (ADLPC = 0)		f	—	3.3	—	MHz		
source	Low power (ADLPC = 1)	Т	f <sub>ADACK</sub>	—	2	—			
Conversion time (including	Short sample (ADLSMP=0)	Р	t	—	20	—	ADCK		
sample time)	Long sample (ADLSMP=1)		t <sub>ADC</sub>	—	40	—	cycles		
Sample time	Short sample (ADLSMP=0)	Р	t	—	3.5	—	ADCK		
Sample une	Long sample (ADLSMP=1)		t <sub>ADS</sub>	—	23.5	—	cycles		
Total unadjusted error	10 bit mode	с	<b>_</b>	—	±1	±2.5	LSB <sup>2</sup>		
8 bit mode			E <sub>TUE</sub>	—	±0.5	±1.0	LOD		
	10 bit mode	Р	DNL	—	±0.5	±1.0	LSB <sup>2</sup>		
Differential non-linearity	8 bit mode	Т	DINE	—	±0.3	±0.5	200		
	Monotor	Monotonicity and No-Missing-Codes guaranteed							
Integral non-linearity	10 bit mode	с	INL	_	±0.5	±1.0	LSB <sup>2</sup>		
integral non-linearity	8 bit mode	U		—	±0.3	±0.5	LOD		
Zero-scale error	10 bit mode	Р	E <sub>ZS</sub>	—	±0.5	±1.5	LSB <sup>2</sup>		
	8 bit mode	Т	⊢zs	—	±0.5	±0.5	LOD		
Full-Scale error	10 bit mode	Р	<b>E</b> .	—	±0.5	±1.5	LSB <sup>2</sup>		
VADIN = VDDA	8 bit mode	Т	E <sub>FS</sub>	—	±0.5	±0.5	LOD		
Quantization error	10 bit mode	D	E	—	—	±0.5	LSB <sup>2</sup>		
	8 bit mode		EQ	_	—	±0.5	LOD		
Input leakage error	10 bit mode	D	F	—	±0.2	±2.5	LSB <sup>2</sup>		
pad leakage <sup>3</sup> * RAS	8 bit mode		E <sub>IL</sub>	—	±0.1	±1	LOD		

<sup>1</sup> Typical values assume Temp = 25 °C, f<sub>ADCK</sub> = 1.0 MHz unless otherwise stated. Typical values are for reference only and are not tested in production.

<sup>2</sup> 1 LSB =  $(V_{REFH} - V_{REFL})/2^{N}$ 

<sup>3</sup> Based on input pad leakage current. Refer to pad electrical.

### 3.13 Flash Specifications

This section provides details about program/erase times and program-erase endurance for the flash memory. For detailed information about program/erase operations, see the reference manual.

Table	16.	Flash	<b>Characteristics</b>
-------	-----	-------	------------------------

Characteristic	Symbol	Min	Typical <sup>1</sup>	Max	Unit
Supply voltage for program/erase	V <sub>DD</sub>	2.7	_	5.5	V

Characteristic	Symbol	Min	Typical <sup>1</sup>	Мах	Unit
Program/Erase voltage	V <sub>PP</sub>	11.8	12	12.2	V
VPP current Program Mass erase	I <sub>VPP_prog</sub> I <sub>VPP_erase</sub>	_		200 100	μ <b>Α</b> μ <b>Α</b>
Supply voltage for read operation 0 < fBus < 10 MHz	V <sub>Read</sub>	1.8	_	5.5	V
Byte program time	t <sub>prog</sub>	20	—	40	μS
Mass erase time	t <sub>me</sub>	500	—		ms
Cumulative program HV time <sup>2</sup>	t <sub>hv</sub>		—	8	ms
Total cumulative HV time (total of tme & thv applied to device)	t <sub>hv_total</sub>	_	—	2	hours
HVEN to program setup time	t <sub>pgs</sub>	10	—		μS
PGM/MASS to HVEN setup time	t <sub>nvs</sub>	5	—	_	μS
HVEN hold time for PGM	t <sub>nvh</sub>	5	—		μs
HVEN hold time for MASS	t <sub>nvh1</sub>	100	—		μS
V <sub>PP</sub> to PGM/MASS setup time	t <sub>vps</sub>	20	—		ns
HVEN to V <sub>PP</sub> hold time	t <sub>vph</sub>	20	—		ns
V <sub>PP</sub> rise time <sup>3</sup>	t <sub>vrs</sub>	200	—		ns
Recovery time	t <sub>rcv</sub>	1	—		μs
Program/erase endurance TL to TH = $-40^{\circ}$ C to $85^{\circ}$ C	_	1000	—	_	cycles
Data retention	t <sub>D_ret</sub>	15	—		years

#### Table 16. Flash Characteristics (continued)

<sup>1</sup> Typicals are measured at 25 °C.

 $^2$  t<sub>hv</sub> is the cumulative high voltage programming time to the same row before next erase. Same address can not be programmed more than twice before next erase.

<sup>3</sup> Fast V<sub>PP</sub> rise time may potentially trigger the ESD protection structure, which may result in over current flowing into the pad and cause permanent damage to the pad. External filtering for the V<sub>PP</sub> power source is recommended. An example V<sub>PP</sub> filter is shown in Figure 22.

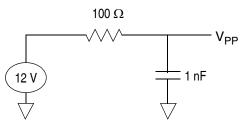
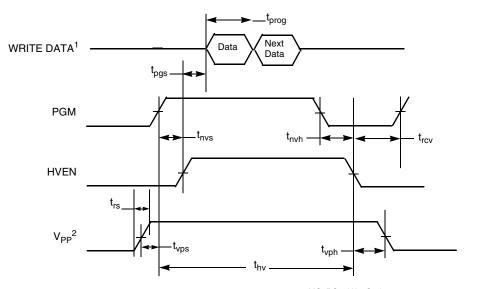
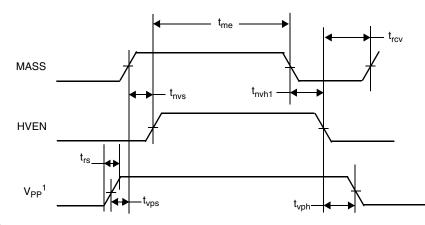


Figure 22. Example V<sub>PP</sub> Filtering



<sup>1</sup> Next Data applies if programming multiple bytes in a single row, refer to  $^{MC9RS08KA8 Series}$  Reference Manual. <sup>2</sup> V<sub>DD</sub> must be at a valid operating voltage before voltage is applied or removed from the V<sub>PP</sub> pin.

Figure 23. Flash Program Timing



 $^{1}$  V<sub>DD</sub> must be at a valid operating voltage before voltage is applied or removed from the V<sub>PP</sub> pin.

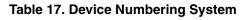
Figure 24. Flash Mass Erase Timing

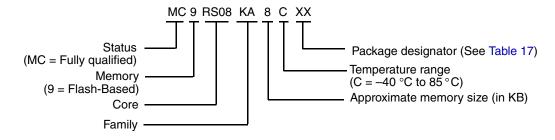
**Ordering Information** 

# 4 Ordering Information

This section contains ordering numbers for MC9RS08KA8 series devices. See below for an example of the device numbering system.

Device Number	Men	nory	Package			
Device Multiper	Flash	RAM	Туре	Designator	Document No.	
			16 PDIP	PG	98ASB42431B	
	8K bytes	254 bytes	16 W-SOIC	WG	98ASB42567B	
MC9RS08KA8 MC9RS08KA4	4K bytes	126 bytes	16 TSSOP	TG	98ASH70247A	
			20 PDIP	PJ	98ASB42899B	
			20 W-SOIC	WJ	98ASB42343B	

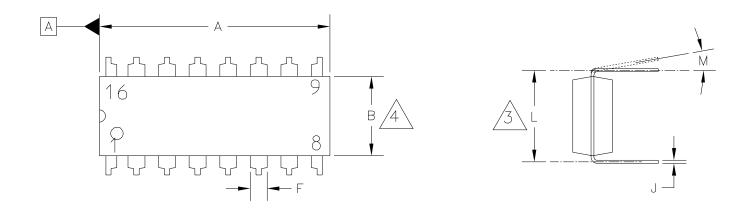


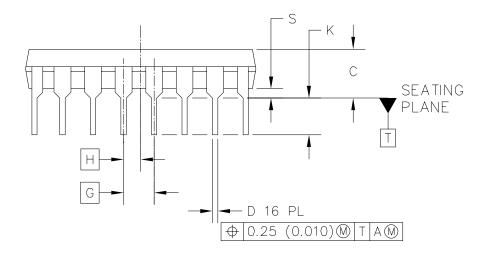


# 5 Mechanical Drawings

This following pages contain mechanical specifications for MC9RS08KA8 series package options.

- 16-pin PDIP (plastic dual in-line pin)
- 16-pin W-SOIC (wide body small outline integrated circuit)
- 16-pin TSSOP (thin shrink sSmall outline package)
- 20-pin PDIP (plastic dual in-line pin)
- 20-pin W-SOIC (wide body small outline integrated circuit)





© FREESCALE SEMICONDUCTOR, INC. All rights reserved.	L OUTLINE	PRINT VERSION NE	IT TO SCALE	
TITLE:		DOCUMENT NE	]: 98ASB42431B	RE∨: T
		CASE NUMBER	2: 648-08	19 MAY 2005
	STANDARD: NE	IN-JEDEC		

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

2. CONTROLLING DIMENSION: INCH.

A DIMENSION TO CENTER OF LEADS WHEN FORMED PARALLEL.

4 dimensions does not include mold flash.

5. ROUNDED CORNERS OPTIONAL.

6. 648-01 THRU -08 OBSOLETE, NEW STANDARD 648-09.

	MILLIM	ETERS	11	NCHES		MILL	IMETERS		INCHES
DIM	MIN	MAX	MIN	MAX	DIM	MIN	MAX	Min	MAX
A	18.80	19.55	0.740	0.770					
В	6.35	6.85	0.250	0.270					
С	3.69	4.44	0.145	0.175					
D	0.39	0.53	0.015	0.021					
F	1.02	1.77	0.040	0.070					
G	2.54	BSC	0.1	00 BSC					
н	1.27	BSC	0.C	50 BSC					
J	0.21	0.38	0.008	0.015					
К	2.80	3.30	0.110	0.130					
L	7.50	7.74	0.295	0.305					
М	0.	10°	0.	10					
S	0.51	1.01	0.020	0.040					
© FF		ICONDUCTOR, I S RESERVED.	NC.	MECHANICA	L OUT	LINE	PRINT VERS	SION NO	DT TO SCALE
TITLE	:					Ment nc	:98ASB4243	1 B	REV: T
		16 LD F	DIP		CASE NUMBER: 648-08 19 MAY 2005				19 MAY 2005
					STANDARD: NON-JEDEC				

### STYLE 1:

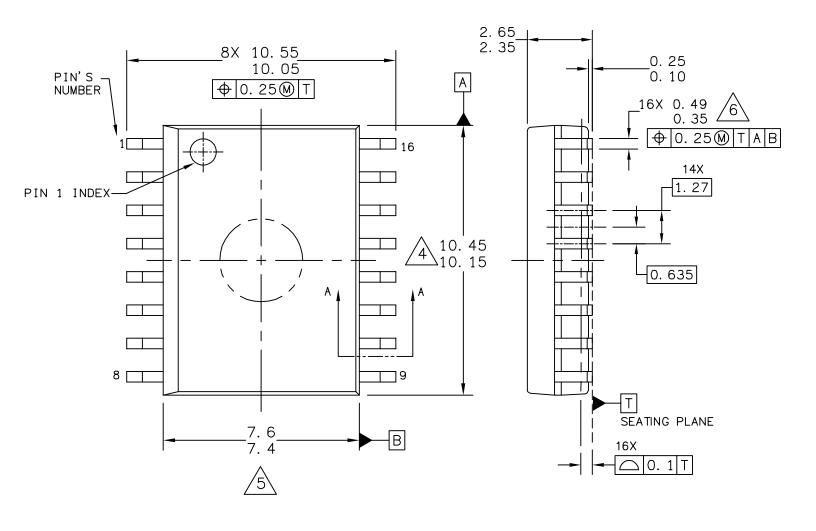
### PIN 1. CATHODE

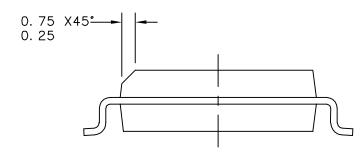
- 2. CATHODE
- 3. CATHODE
- 4. CATHODE
- 5. CATHODE
- 6. CATHODE
- 7. CATHODE
- 8. CATHODE
- 9. ANODE
- 10. ANODE
- 11. ANODE
- 12. ANODE
- 13. ANODE
- 14. ANODE
- 15. ANODE
- 16. ANODE

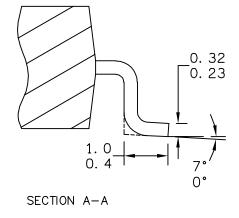
STYLE 2:

- PIN 1. COMMON DRAIN
  - 2. COMMON DRAIN
  - 3. COMMON DRAIN
  - 4. COMMON DRAIN
  - 5. COMMON DRAIN
  - 6. COMMON DRAIN
  - 7. COMMON DRAIN
  - 8. COMMON DRAIN
  - 9. GATE
  - 10. SOURCE
  - 11. GATE
  - 12. SOURCE
  - 13. GATE
  - 14. SOURCE
  - 15. GATE
  - 16. SOURCE

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TITLE:		DOCUMENT NO	): 98ASB42431B	REV: T
16 LD PDIP		CASE NUMBER	8:648-08	19 MAY 2005
		STANDARD: NO	N-JEDEC	



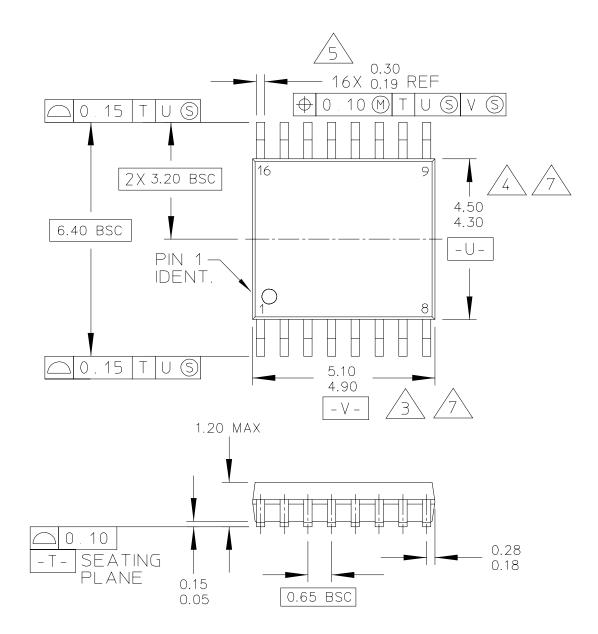




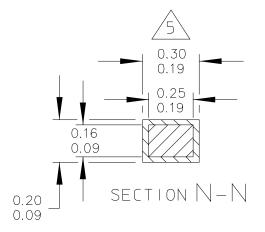
© FREESCALE SEMICONDUCTOR, INC. ALL RIGHTS RESERVED.	L OUTLINE	PRINT VERSION NO	DT TO SCALE	
TITLE:		DOCUMENT NO	): 98ASB42567B	REV: F
16LD SOIC W/B, 1.27 PITCH Case-outline		CASE NUMBER: 751G-04 02 JUN 20		02 JUN 2005
		STANDARD: JE	DEC MS-013AA	

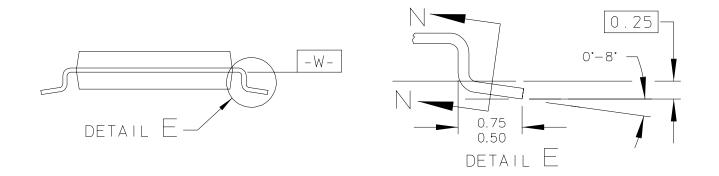
- 1. DIMENSIONS ARE IN MILLIMETERS.
- 2. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.
- 3. DATUMS A AND B TO BE DETERMINED AT THE PLANE WHERE THE BOTTOM OF THE LEADS EXIT THE PLASTIC BODY.
- 4. THIS DIMENSION DOES NOT INCLUDE MOLD FLASH, PROTRUSION OR GATE BURRS. MOLD FLASH, PROTRUSION OR GATE BURRS SHALL NOT EXCEED 0.15 MM PER SIDE. THIS DIMENSION IS DETERMINED AT THE PLANE WHERE THE BOTTOM OF THE LEADS EXIT THE PLASTIC BODY.
- 5. THIS DIMENSION DOES NOT INCLUDE INTER-LEAD FLASH OR PROTRUSIONS. INTER-LEAD FLASH AND PROTRUSIONS SHALL NOT EXCEED 0.25 MM PER SIDE. THIS DIMENSION IS DETERMINED AT THE PLANE WHERE THE BOTTOM OF THE LEADS EXIT THE PLASTIC BODY.
- 6. THIS DIMENSION DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL NOT CAUSE THE LEAD WIDTH TO EXCEED 0.62 mm.

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TITLE:		DOCUMENT NO	: 98ASB42567B	REV: F
16LD SOIC W/B, 1.27 CASE OUTLINE	CASE NUMBER	2: 751G-04	02 JUN 2005	
		STANDARD: JEDEC MS-013AA		



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TITLE:	DOCUMENT NE	]: 98ASH70247A	REV∶B
16 LD TSSOP, PITCH 0.6	CASE NUMBER: 948F-01 19 MAY 20		
	STANDARD: JE	EDEC	





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TITLE:	DOCUMENT NE	]: 98ASH70247A	RE∨: B	
16 LD TSSOP. PITCH 0.	CASE NUMBER: 948F-01 19 MAY 200			
	STANDARD: JE	DEC		

1. CONTROLLING DIMENSION: MILLIMETER

2. DIMENSIONS AND TOLERANCES PER ANSI Y14.5M-1982.

<u>/</u>3 DIMENSION DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE.

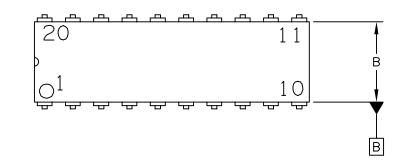
4 DIMENSION DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 PER SIDE

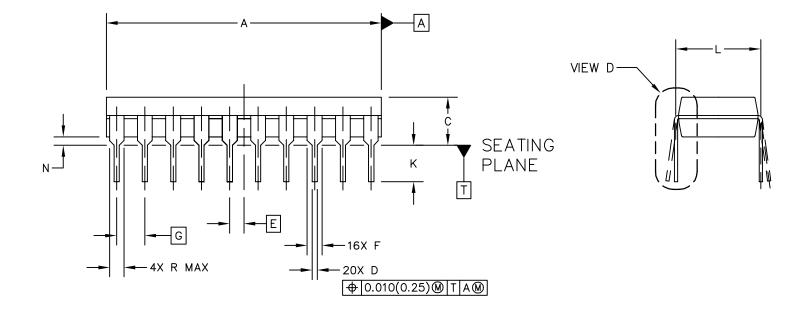
5 DIMENSION DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF THE DIMENSION AT MAXIMUM MATERIAL CONDITION.

6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

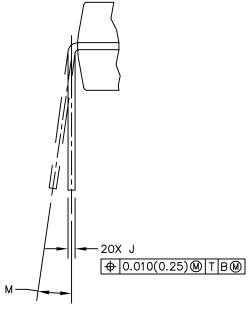
 $^{/7}$  dimensions are to be determined at datum plane [-w-

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TITLE:	DOCUMENT NE	]: 98ASH70247A	RE∨: B	
16 LD TSSOP, PITCH 0.6	CASE NUMBER: 948F-01 19 MAY 200			
	STANDARD: JE	DEC		





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TITLE:		DOCUMENT NE	]: 98ASB42899B	RE∨: B
20LD .300 PDI		CASE NUMBER	R: 738C-01	24 MAY 2005
		STANDARD: NE	IN-JEDEC	

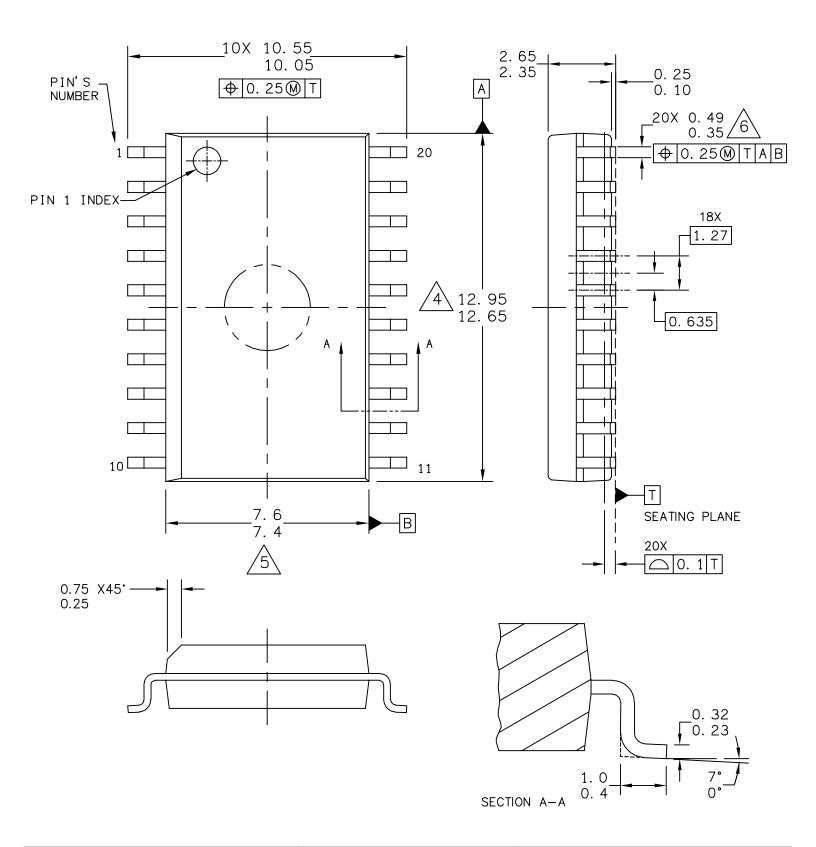


VIEW D

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TITLE:	DOCUMENT NO	]: 98ASB42899B	RE∨: B
20LD .300 PDIF	CASE NUMBER	R: 738C-01	24 MAY 2005
	STANDARD: NE	IN-JEDEC	

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M 1994.
- 2. CONTROLLING DIMENSION: INCH.
- 3. DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.
- 4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.

DIM	MILLIM MIN	IETERS MAX	DIM	IN MIN	ICHES MAX	DIM	MILLIM	ETERS MAX	DIM	MI	INCHES IN MAX
А	24.39	24.99		0.960	0.984						
В	6.96	7.49		0.274	0.295						
С	3.56	5.08		0.140	0.200						
D	0.38	0.56		0.015	0.022						
Е	1.27	BSC		0.05	0 BSC						
F	1.14	1.52		0.045	0.060						
G	2.54	BSC		0.10	0 BSC						
J	0.20	0.38		0.008	0.015						
К	2.79	3.76		0.110	0.148						
L	7.62 E	SC		0.300	) BSC						
М	0.	15°		0.	15 <b>·</b>						
Ν	0.50	1.01		0.020	0.040						
R	•••••	1.29		•••••	0.051						
		SEMICONDUC IGHTS RESE		NC.	MECHANI	CAL	OUTLINE	PRINT	VERS	ION NO	T TO SCALE
TITL	_E:					I	DOCUMENT NE	]: 98ASB42	2899I	3	RE∨: B
		20LD	₹0	0 PDIF	C		ASE NUMBER	R 738C−01			24 MAY 2005
		ZULD				S	STANDARD: NE	IN-JEDEC			



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TITLE:		DOCUMENT NO	): 98ASB42343B	REV: J
20LD SOIC W/B, 1. CASE-OUTLI	CASE NUMBER	R: 751D-07	23 MAR 2005	
		STANDARD: JE	DEC MS-013AC	

- 1. DIMENSIONS ARE IN MILLIMETERS.
- 2. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.
- 3. DATUMS A AND B TO BE DETERMINED AT THE PLANE WHERE THE BOTTOM OF THE LEADS EXIT THE PLASTIC BODY.
- 4. THIS DIMENSION DOES NOT INCLUDE MOLD FLASH, PROTRUSION OR GATE BURRS. MOLD FLASH, PROTRUSION OR GATE BURRS SHALL NOT EXCEED 0.15 MM PER SIDE. THIS DIMENSION IS DETERMINED AT THE PLANE WHERE THE BOTTOM OF THE LEADS EXIT THE PLASTIC BODY.
- 5. THIS DIMENSION DOES NOT INCLUDE INTER-LEAD FLASH OR PROTRUSIONS. INTER-LEAD FLASH AND PROTRUSIONS SHALL NOT EXCEED 0.25 MM PER SIDE. THIS DIMENSION IS DETERMINED AT THE PLANE WHERE THE BOTTOM OF THE LEADS EXIT THE PLASTIC BODY.
- 6. THIS DIMENSION DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL NOT CAUSE THE LEAD WIDTH TO EXCEED 0.62 mm.

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TITLE:		DOCUMENT NO	: 98ASB42343B	REV: J
20LD SOIC W/B, 1.27 PITCH, CASE OUTLINE		CASE NUMBER	2: 751D-07	23 MAR 2005
	-	STANDARD: JEDEC MS-013AC		

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